

Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+PNP)

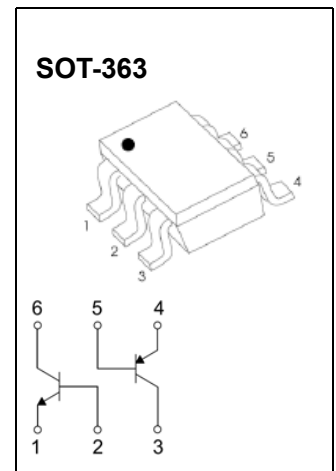
FEATURES

- Complementary Pair
- One 4401-Type NPN
One 4403-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

MAKING: K13

Maximum Ratings, NPN 4401 Section (Ta = 25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	0.6	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C



NPN 4401 ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100 μA, I _E =0	60		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100 μA, I _C =0	6		V
Collector cut-off current	I _{CBO}	V _{CB} = 50 V, I _E =0		0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 35 V, I _B =0		0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0		0.1	μA
DC current gain	h _{FE(1)}	V _{CE} = 1V, I _C = 0.1mA	20		
	h _{FE(2)}	V _{CE} = 1V, I _C = 1mA	40		
	h _{FE(3)}	V _{CE} = 1V, I _C = 10mA	80		
	h _{FE(4)}	V _{CE} = 1V, I _C = 150mA	100	300	
	h _{FE(5)}	V _{CE} = 2V, I _C = 500mA	40		
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =150 mA, I _B = 15mA		0.4	V
	V _{CE(sat)2}	I _C =500 mA, I _B = 50mA		0.75	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C = 150 mA, I _B = 15mA	0.75	0.95	V
	V _{BE(sat)2}	I _C = 500 mA, I _B = 50mA		1.2	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 20mA, f=100MHz	250		MHz
Output Capacitance	C _{ob}	V _{CB} =5V, I _E = 0, f=1MHz		6.5	pF
Delay time	t _d	V _{CC} =30V, V _{BE} =2.0V, I _C =150mA, I _{B1} =15mA		15	nS
Rise time	t _r			20	nS
Storage time	t _s	V _{CC} =30V, I _C =150mA, I _{B1} =- I _{B2} = 15mA		225	nS
Fall time	t _f			30	nS

Maximum Ratings, PNP 4403 Section (Ta = 25°C unless otherwise specified)

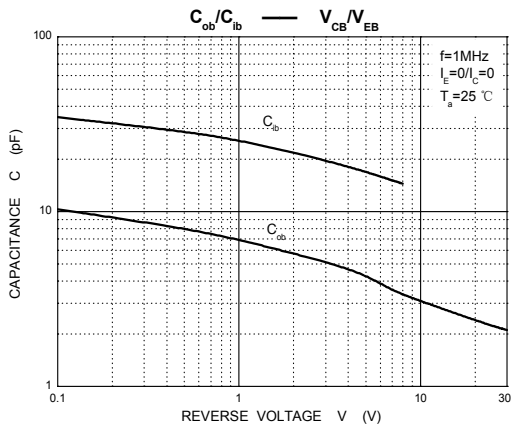
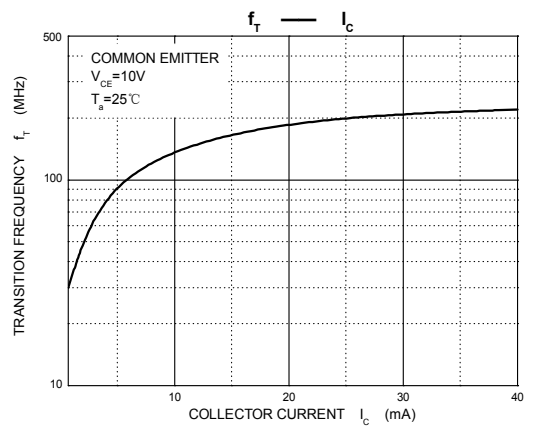
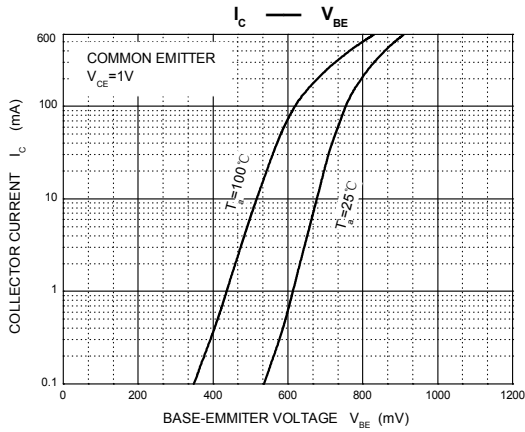
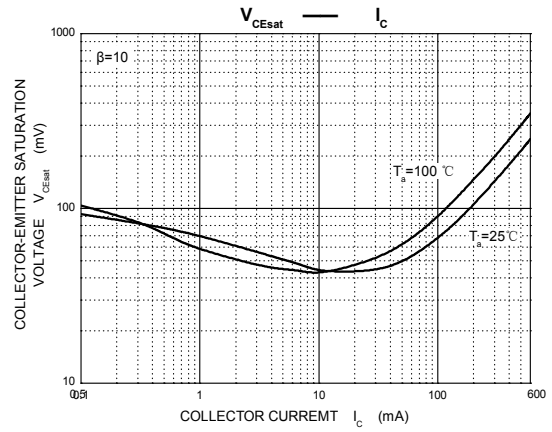
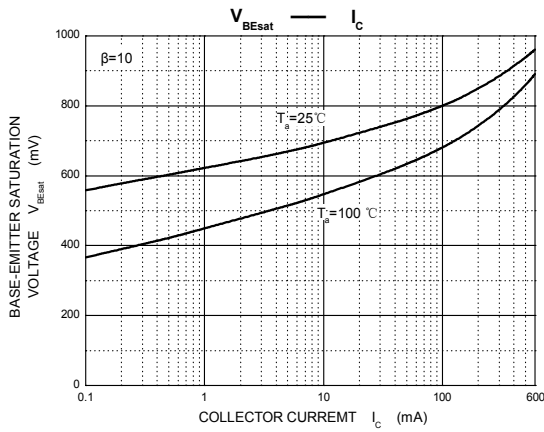
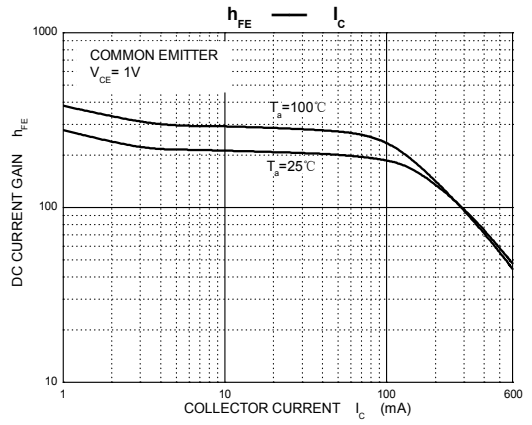
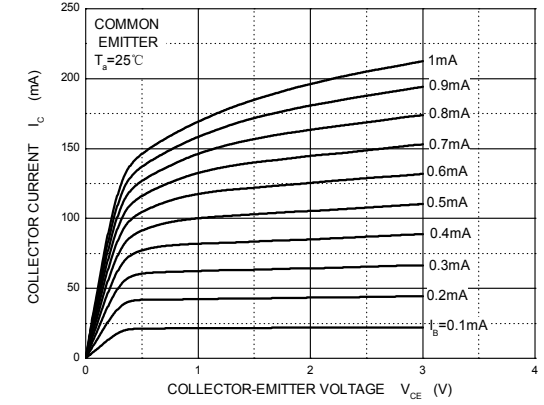
Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.6	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C

PNP 4403 ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E = 0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B = 0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -35 V, I _B = 0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} = -1 V, I _C = -0.1mA	30			
	h _{FE(2)}	V _{CE} = -1 V, I _C = -1mA	60			
	h _{FE(3)}	V _{CE} = -1 V, I _C = -10mA	100			
	h _{FE(4)}	V _{CE} = -2 V, I _C = -150mA	100		300	
	h _{FE(5)}	V _{CE} = -2 V, I _C = -500mA	20			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C = -150 mA, I _B = -15mA			-0.4	V
	V _{CE(sat)2}	I _C = -500 mA, I _B = -50mA			-0.75	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C = -150 mA, I _B = -15mA	-0.75		-0.95	V
	V _{BE(sat)2}	I _C = -500 mA, I _B = -50mA			-1.3	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -20mA f = 100MHz	200			MHz
Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0 f = 1MHz			8.5	pF
Delay time	t _d	V _{CC} = -30V, V _{BE} = -2V			15	nS
Rise time	t _r	I _C = -150mA, I _{B1} = -15mA			20	nS
Storage time	t _s	V _{CC} = -30V, I _C = -150mA			225	nS
Fall time	t _f	I _{B1} = -I _{B2} = -15mA			30	nS

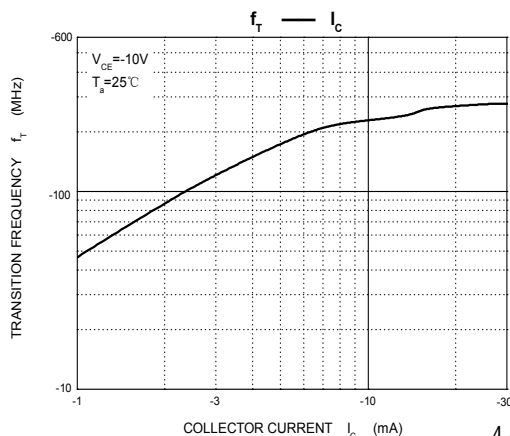
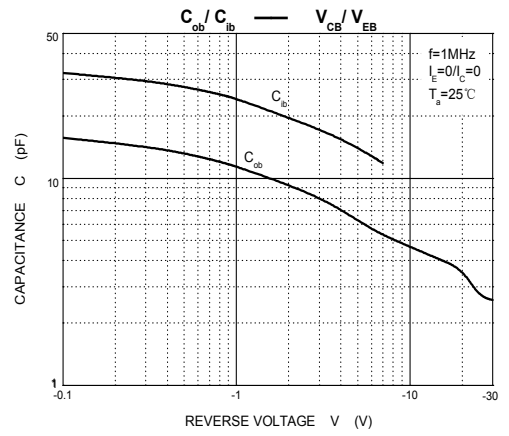
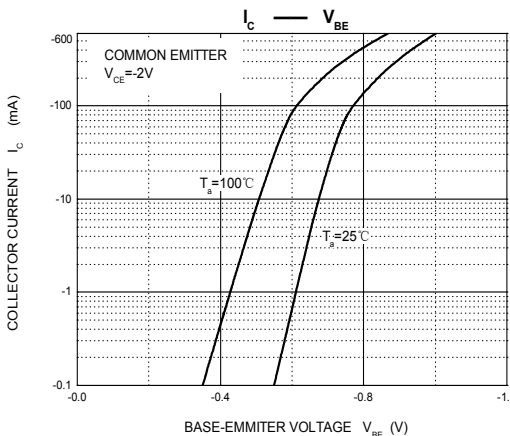
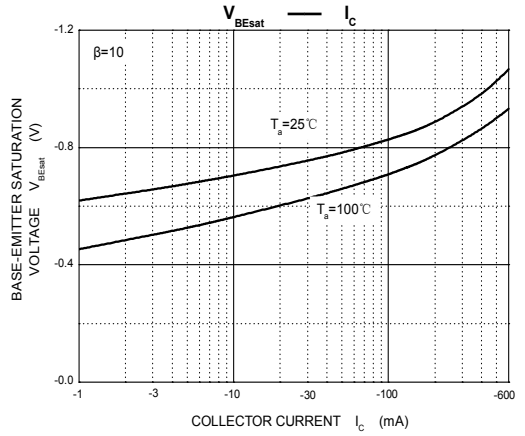
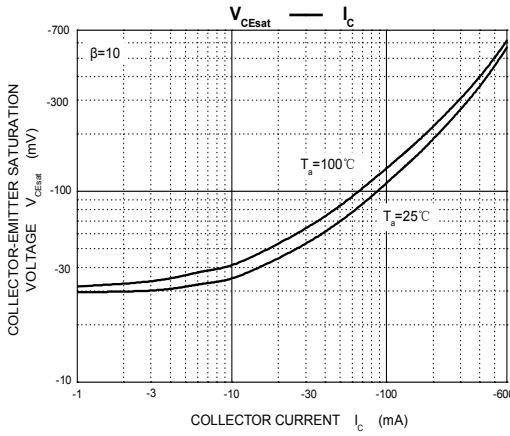
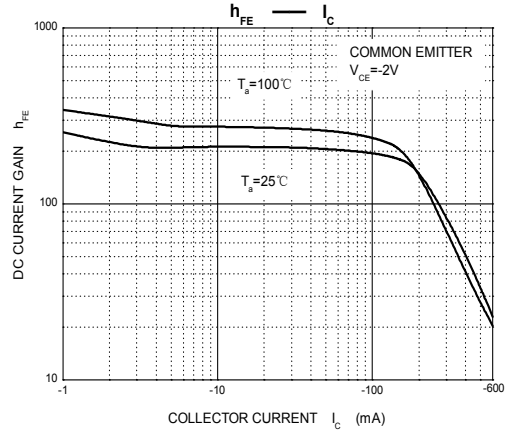
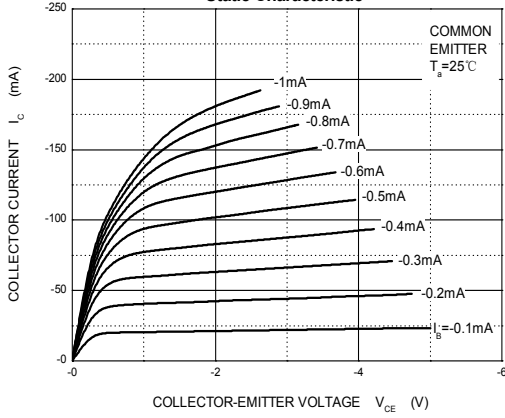
NPN Transistor

Static Characteristic



PNP Transistor

Static Characteristic



SOT-363-Package Outline Dimensions

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